

ABSTRACT OF THE DISCLOSURE

This invention provides a semiconductor device that can ensure that stress on the nitride film is not increased or is reduced, and that can prevent an increase in interconnection capacity. The semiconductor device comprises a underlayer, a base oxide film that is formed on this underlayer, a nitride film pattern with a hole pattern that is provided on this base oxide film, holes that penetrate the base oxide film, an upper oxide film provided on the base oxide film to cover the nitride film pattern, wiring grooves provided through the upper oxide film in which part of the nitride film pattern including the hole pattern is exposed, and wiring metal that fills the holes and wiring grooves. The nitride film pattern is formed with such a shape and size that surrounds the outside of the wiring grooves and is separate from neighbouring nitride film patterns.